



SOT-89-3L Plastic-Encapsulate Transistors

2SB1386 TRANSISTOR (PNP)

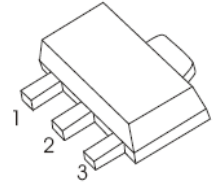
FEATURES

- Low collector saturation voltage
- Excellent current-to-gain characteristics

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-30	V
V _{CE0}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Continuous Collector Current	-5	A
I _{CP} *	Pulsed Collector Current	-10	A
P _C	Collector Power Dissipation	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

SOT-89-3L



1. BASE
2. COLLECTOR
3. EMITTER

*Single pulse, P_w=10ms

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-500mA	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-4A, I _B =-100mA			-1	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-50mA, f=30MHz		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-20V, I _E =0, f=1MHz		60		pF

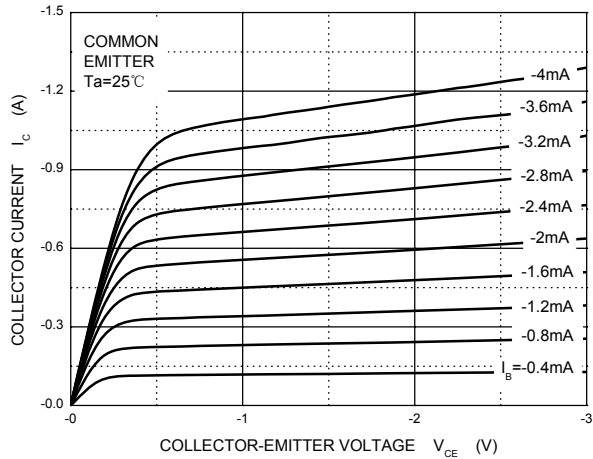
CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BHP	BHQ	BHR

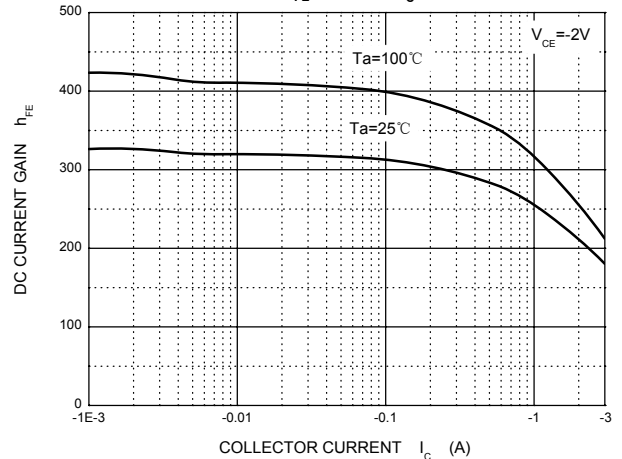
Typical Characteristics

2SB1386

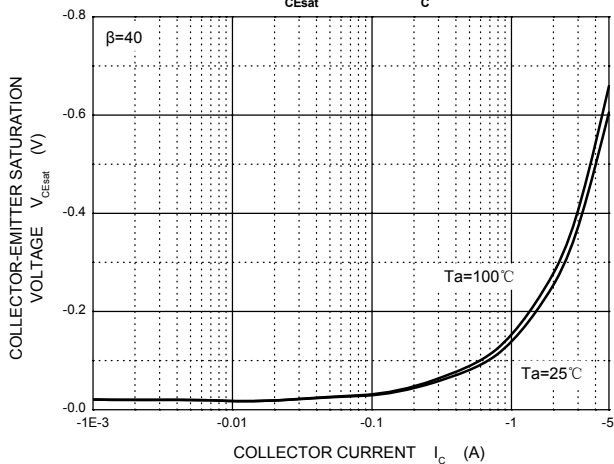
Static Characteristic



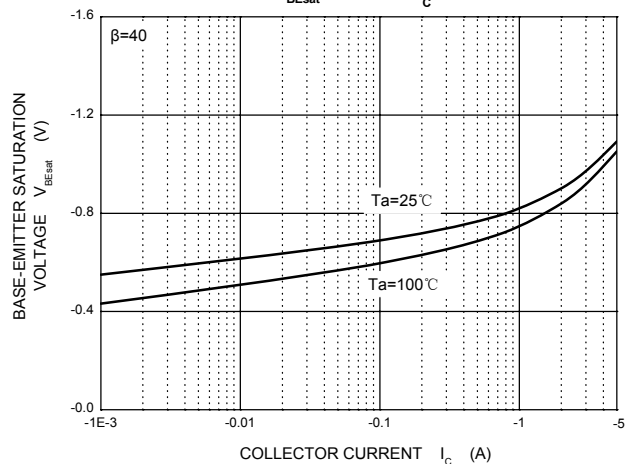
h_{FE} — I_c



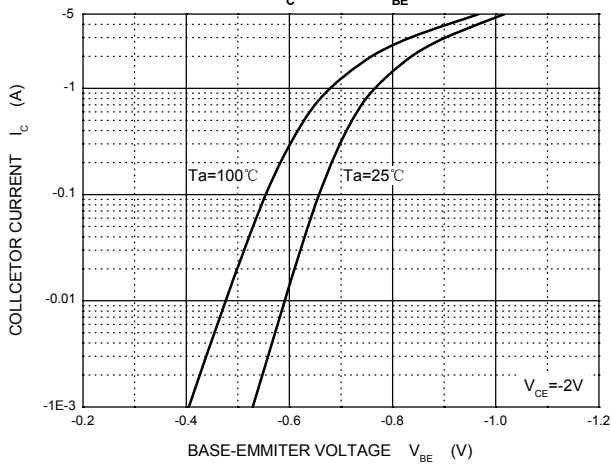
V_{CEsat} — I_c



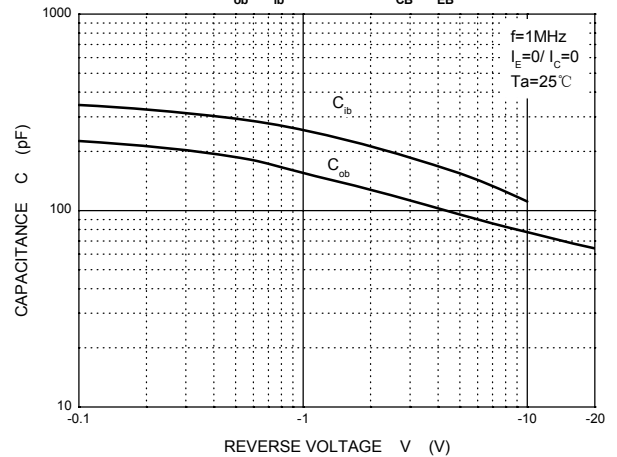
V_{BEsat} — I_c



I_c — V_{BE}



C_{ob}/C_{ib} — V_{CB}/V_{EB}



P_c — T_a

